2SB1001

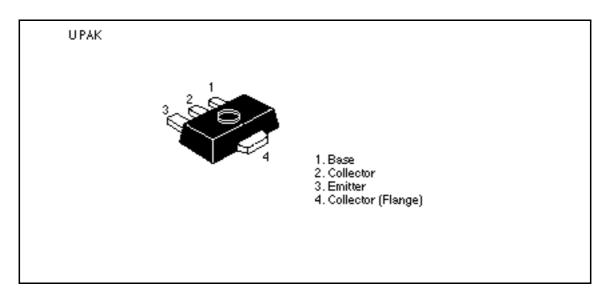
Silicon PNP Epitaxial

HITACHI

Application

- Low frequency power amplifier
- Complementary pair with 2SD1367

Outline





2SB1001

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

| Item | Symbol | Ratings | Unit |
|------------------------------|-------------------------|-------------|------|
| Collector to base voltage | V_{CBO} | -20 | V |
| Collector to emitter voltage | V_{CEO} | –16 | V |
| Emitter to base voltage | V_{EBO} | – 6 | V |
| Collector current | I _c | -2 | А |
| Collector peak current | i _{C(peak)} *1 | -3 | А |
| Collector power dissipation | P _c *² | 1 | W |
| Junction temperature | Tj | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes: 1. PW 10 ms, Duty cycle 20%

2. Value on the alumina ceramic board (12.5 \times 20 \times 0.7 mm)

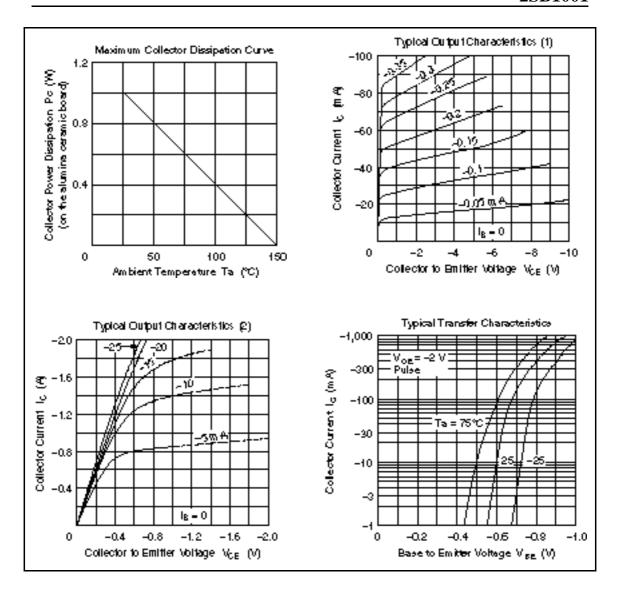
Electrical Characteristics ($Ta = 25^{\circ}C$)

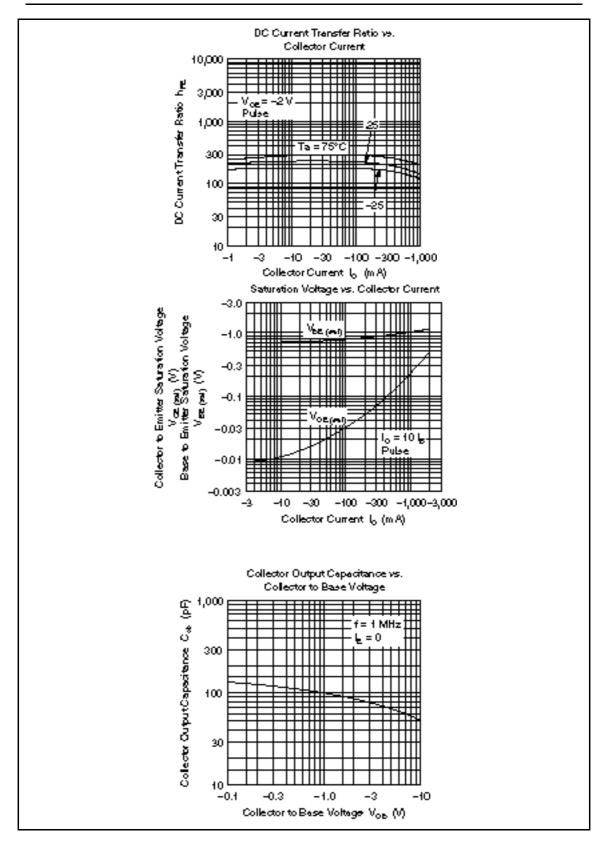
| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|---|----------------------|-----|-------|------|------|--|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | -20 | _ | _ | V | $I_{c} = -10 \ \mu A, \ I_{E} = 0$ |
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | -16 | _ | _ | V | $I_C = -1 \text{ mA}, R_{BE} =$ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | -6 | _ | _ | V | $I_{E} = -10 \ \mu A, \ I_{C} = 0$ |
| Collector cutoff current | I _{CBO} | _ | _ | -0.1 | μΑ | $V_{CB} = -16 \text{ V}, I_{E} = 0$ |
| Emitter cutoff current | I _{EBO} | _ | _ | -0.1 | μΑ | $V_{EB} = -5 \text{ V}, I_{C} = 0$ |
| DC current transfer ratio | h _{FE} *1 | 100 | _ | 320 | | $V_{CE} = -2 \text{ V},$ $I_{C} = -0.1 \text{ A (Pulse test)}$ |
| Collector to emitter saturation voltage | $V_{\text{CE(sat)}}$ | _ | -0.15 | -0.3 | V | $I_C = -1 A$, $I_B = -0.1 A$ (Pulse test) |
| Base to emitter saturation voltage | $V_{BE(sat)}$ | _ | -1.0 | -1.2 | V | $I_C = -1 A$, $I_B = -0.1 A$ (Pulse test) |
| Gain bandwidth product | f _T | _ | 150 | | MHz | $V_{CE} = -2 V$, $I_{C} = -10 \text{ mA}$ |
| Collector output capacitance | Cob | _ | 50 | _ | pF | $V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz |

Note: 1. The 2SB1001 is grouped by h_{FE} as follows.

| Mark | ВН | BJ |
|-----------------|------------|------------|
| h _{FE} | 100 to 200 | 160 to 320 |

2SB1001





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